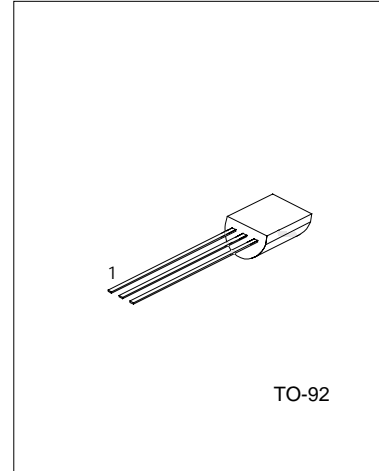


FEATURES

- * Collector-Base Voltage: $V(BR)_{CBO}=600V$
- * Collector Current: $I_C=0.2A$



1: BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	600	V
Collector-emitter voltage	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	200	mA
Collector power dissipation	P_C	750	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V(BR)_{CBO}$	$I_C=100\mu A, I_E=0$	600			V
Collector-Emitter Breakdown Voltage	$V(BR)_{CEO}$	$I_C=1mA, I_B=0$	400			V
Emitter-Base Breakdown Voltage	$V(BR)_{EBO}$	$I_E=100\mu A, I_C=0$	7			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=600V, I_E=0$			100	μA
Collector Cut-off Current	I_{CEO}	$V_{CE}=400V, I_B=0$			200	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=20V, I_C=20mA$	10		70	
	$h_{FE(2)}$	$V_{CE}=10V, I_C=0.25mA$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=10mA$			0.5	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=10mA$			1.2	V
Base-emitter Voltage	V_{BE}	$I_E=100mA$			1.1	V
Transition Frequency	f_T	$V_{CE}=20V, I_C=20mA, f=1MHz$	8			MHz
Fall Time	t_F	$I_C=50mA, I_{B1}=-I_{B2}=5mA,$			0.3	μs
Storage Time	t_S	$V_{CC}=45V$			1.5	μs

CLASSIFICATION OF hFE

RANK	A	B	C	D	E	F	G	H	I	J	K	L
RANGE	10-15	15-20	20-25	25-30	30-35	35-40	40-45	45-50	50-55	55-60	60-65	65-70

TYPICAL CHARACTERISTICS

